



Features

- High voltage, medium current silicon diode
- RoHS compliant to Directive 2011/65/EC, Article 4(1), Annex II, Annex III, 7(a) and EU RoHS Directive (EU) 2015/863 of March 2015, Amending Annex II.



DEVICE ELECTRICAL CHARACTERISTICS

(25°C ambient temperature unless stated otherwise)

	Conditions	Symbol	Value
Maximum Repetitive Peak Reverse Voltage	-	V_{RRM}	45,000 Volts
Average Forward Current Maximum	$T_{Air} = 55^{\circ}C$	I_{FAVM}	100 mAmps
Maximum Forward Voltage Drop	$I_F = 100$ mAmps	V_F	40 Volts
Maximum Surge Current Rating	8.3msec, half sine	I_{FSM}	30 Amps
Maximum Reverse Current	at rated V_{RRM}	I_R	5.0 μA
Maximum Junction Temperature	-	T_J	125°C
Storage Temperature Range	-	T_{STG}	-55°C to 150°C

MECHANICAL DATA

		Min.		Max.	
		in.	mm	in.	mm
Body Length	A	-	-	0.87	22.1
Body Diameter	D	-	-	0.30	7.6
Lead Length	B	0.945	24.0	-	-
Lead Diameter	C	-	-	0.050	1.27

